

internal factory that is TS16949, ISO-9001 and ISO-14000 certified.

Title of Change:	Qualification of Niigata Fab (Japan) as the additional wafer source for Bipolar Power Planar Transistors.		
Proposed first ship date:	5 December 2017 or earlier upon customer approval		
Contact information:	Contact your local ON Semiconductor Sales Office or < Hiroshi.Koizumi@onsemi.com>		
Samples:	Contact your local ON Semiconductor Sales Office		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or < Hiroshi.Koizumi@onsemi.com>.		
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>		
Change Part Identification:	Affected products will be identified with date code.		
Change category:	🛛 Wafer Fab Change 🔲 Assembly Change 🔲 Test Change 🔲 Other		
Change Sub-Category(s): Manufacturing Site Change/ Manufacturing Process Char Sites Affected: All site(s) not ap			
	ON Niigata, Japan		
Description and Purpose:			
This is the Final Notification by ON Semiconductor notifying customers of its plan to add Niigata Fab (Japan) as the qualified wafer source for Bipolar Power Planar Transistor.			
-	Semiconductor owned wafer fab that has been producing products for ON Semiconductor. Several existing ductor's product families are currently sourced from Niigata Fab. ON Semiconductor Niigata Wafer Fab is an		

Qualification tests are designed to show that the reliability of the impacted devices will continue to meet or exceed ON Semiconductor standards



Reliability Data Summary:

QV DEVICE NAME <u>MJE5852G</u> RMS: <u>23106</u> PACKAGE: TO220

PACKAGE: 10220				
Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=150°C, 80% max rated V	1008 hrs	0/80
Autoclave	JESD22-A102	Ta=121°C, RH=100% 15psig	96 hrs	0/80
H3TRB	JESD22-A101	Ta= 85°C, 85% RH, 80%bias	1008 hrs	0/80
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 3.5 min	8572 cyc	0/80
TC	JESD22-A104	Ta= -65°C to +150°C	1000 сус	0/80
RSH	JESD22- B106	Ta = 260C, 10 sec		0/30

QV DEVICE NAME MJD340T4G RMS: 23107

PACKAGE: DPAK

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=150°C, 80% max rated V	1008 hrs	0/160
Autoclave+PC	JESD22-A102	Ta=121°C, RH=100% 15psig	96 hrs	0/160
H3TRB+PC	JESD22-A101	Ta= 85°C, 85% RH, 80%bias	504 hrs	0/160
IOL+PC	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 2 min	7500 cyc	0/160
TC+PC	JESD22-A104	Ta= -65°C to +150°C	1000 сус	0/160
RSH	JESD22- B106	Ta = 260C, 10 sec		0/60

QV DEVICE NAME NJW0281G

RMS: <u>34697</u> **PACKAGE:** TO-3P

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=150°C, 80% max rated V	1008 hrs	0/80
H3TRB	JESD22-A101	Ta= 85°C, 85% RH, 80%bias	1008 hrs	0/80
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 2 min	6000 cyc	0/80
тс	JESD22-A104	Ta= -55°C to +150°C	1000 сус	0/80

Electrical Characteristic Summary:

Electrical characteristics are not impacted.



of affected Standard Parts:		
Part Number	Qualification Vehicle	
MJD210G		
MJD210RLG		
MJD210T4G		
MJD253-1G		
MJD253T4G		
MJD350T4G	_	
MJD5731T4G	_	
MJE15035G	MJD340T4G/MJE5852G	
MJE210G		
MJE253G		
MJE5730G		
MJE5731AG	1	
MJE5731G		
MMJT350T1G		
NJD1718T4G		
2N6338G		
2N6341G		
BUV26G		
BUV27G		
MJD200G		
MJD200RLG		
MJD200T4G		
MJD243G	NJW0281G	
MJD243T4G		
MJD44E3T4G	7	
MJE200G		
MJE243G		
MJE270G		
NJW44H11G	7	
NJL0281DG		